## MOSFET - Power, Dual N-Channel, DUAL SO-8FL

60 V, 29.7 mΩ, 19 A

## NVMFD030N06C

#### Features

- Small Footprint (5x6 mm) for Compact Design
- Low R<sub>DS(on)</sub> to Minimize Conduction Losses
- Low Q<sub>G</sub> and Capacitance to Minimize Driver Losses
- NVMFWD030N06C Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Typical Applications**

- Power Tools, Battery Operated Vacuums
- UAV/Drones, Material Handling
- BMS/Storage, Home Automation

#### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}C$ unless otherwise stated)

	- (-)					
Para	Symbol	Value	Units			
Drain-to-Source Voltage			V <sub>DSS</sub>	60	V	
Gate-to-Source Voltage			V <sub>GS</sub>	±20	V	
Continuous Drain	Steady State	$T_{C} = 25^{\circ}C$	۱ <sub>D</sub>	19	А	
Current R <sub>θJC</sub> (Notes 1, 3)	Sidle	T <sub>C</sub> = 100°C		13		
Power Dissipation			PD	23	W	
$R_{\theta JC}$ (Note 1)	State	$T_{C} = 100^{\circ}C$		11		
Continuous Drain	Steady State	T <sub>A</sub> = 25°C	I <sub>D</sub>	7	А	
Current R <sub>θJA</sub> (Notes 1, 2, 3)	Slale	T <sub>A</sub> = 100°C		5		
Power Dissipation	Steady	$T_A = 25^{\circ}C$	PD	3.2	W	
$R_{\theta JA}$ (Notes 1, 2)	State	State T <sub>A</sub> = 100°C		1.6		
Pulsed Drain Current	T <sub>A</sub> = 25°0	C, t <sub>p</sub> = 10 μs	I <sub>DM</sub>	63	А	
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	–55 to +175	°C	
Source Current (Body Diode)			۱ <sub>S</sub>	19	А	
Single Pulse Drain-to-Source Avalanche Energy ( $I_L = 4.4 A_{pk}$ )			E <sub>AS</sub>	10	mJ	
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)			ΤL	260	°C	
			•			

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

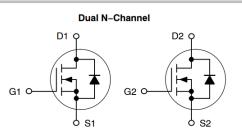
- 2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
- 3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

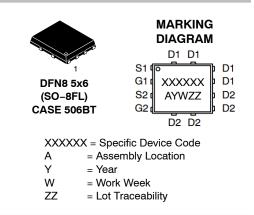


### **ON Semiconductor®**

#### www.onsemi.com

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX
60 V	29.7 mΩ @ 10 V	19 A





#### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

#### THERMAL RESISTANCE RATINGS

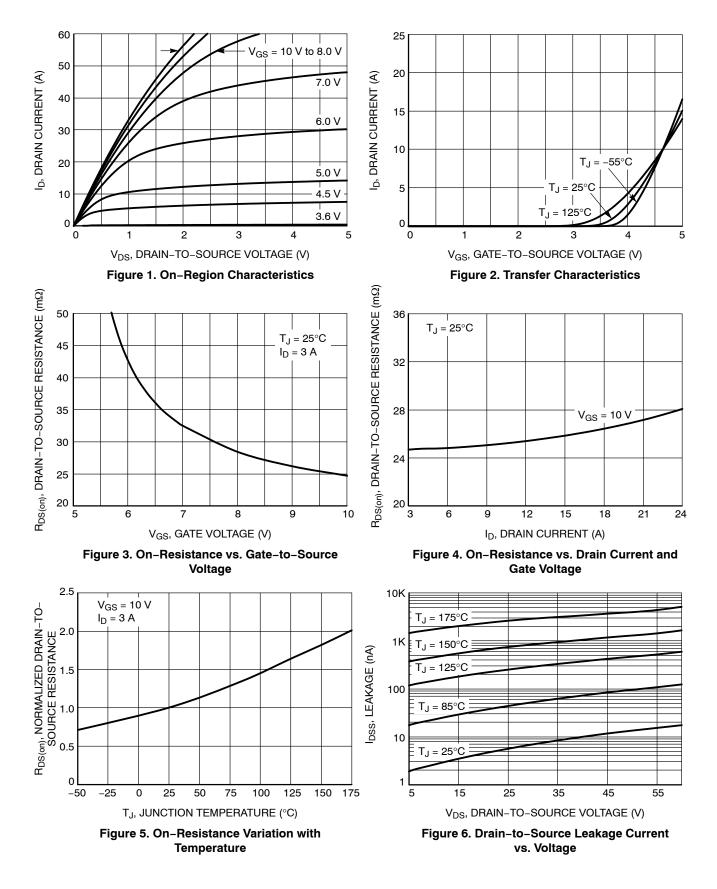
Parameter	Symbol	Мах	Unit	
Junction-to-Case - Steady State (Note 2)	R <sub>θJC</sub> 6.3		°C M/	
Junction-to-Ambient - Steady State (Note 2)	R <sub>0JA</sub>	46.6	°C/W	

#### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise specified)

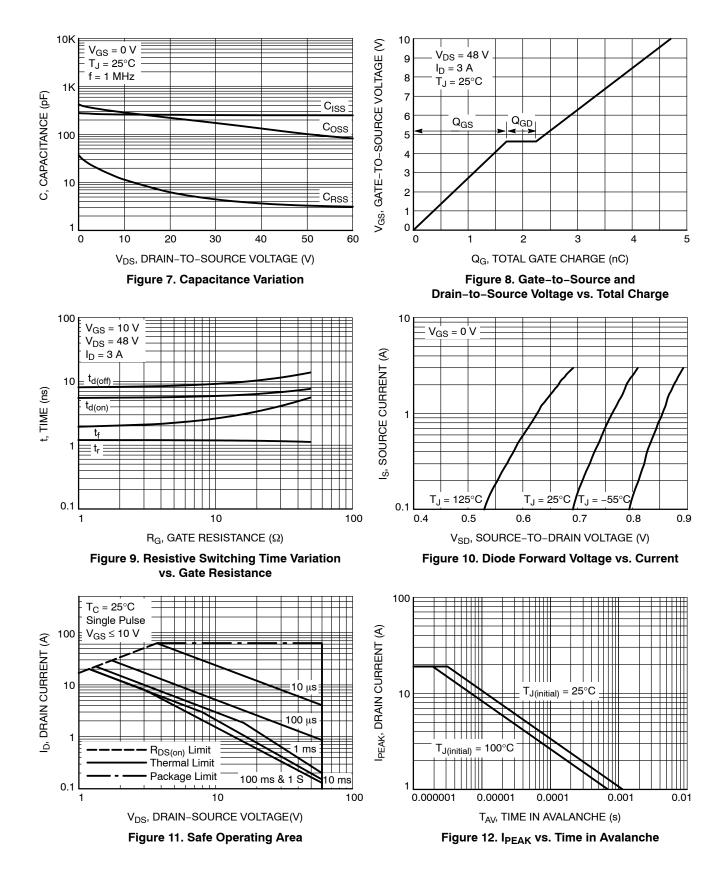
Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS	•I						•
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS}$ = 0 V, $I_D$ = 250 $\mu$ A		60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> / T <sub>J</sub>	$I_D = 250 \ \mu\text{A}, \text{ ref to } 25^\circ\text{C}$			-7.9		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V,$ $T_{J} = 25^{\circ}C$				10	μΑ
		$V_{DS} = 60 \text{ V}$ $T_{J} = 125^{\circ}\text{C}$			250		
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 20 V				100	nA
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D = 13 \ \mu A$		2.0		4.0	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> / T <sub>J</sub>	$I_D = 13 \ \mu\text{A}$ , ref to $25^{\circ}\text{C}$			-7.8		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, \ \text{I}_{D} = 3 \text{ A}$			24.7	29.7	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 3 A			8.5		S
Gate Resistance	R <sub>G</sub>	$T_A = 25^{\circ}C$			1.5		Ω
CHARGES & CAPACITANCES							
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 30 V			255		pF
Output Capacitance	C <sub>OSS</sub>				173		
Reverse Capacitance	C <sub>RSS</sub>				4.4		
Total Gate Charge	Q <sub>G(TOT)</sub>	$V_{GS}$ = 10 V, $V_{DS}$ = 48 V, $I_{D}$ = 3 A			4.7		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>				1.1		-
Gate-to-Source Charge	Q <sub>GS</sub>				1.7		
Gate-to-Drain Charge	Q <sub>GD</sub>				0.54		
SWITCHING CHARACTERISTICS (Not	e 3)						
Turn-On Delay Time	t <sub>d(ON)</sub>				5.7		ns
Rise Time	t <sub>r</sub>	V <sub>GS</sub> = 10 V,	V <sub>DS</sub> = 48 V,		1.2		]
Turn-Off Delay Time	t <sub>d(OFF)</sub>	$I_D = 3A, R_G = 6 \Omega$			8.7		
Fall Time	t <sub>f</sub>				2.3		
DRAIN-SOURCE DIODE CHARACTER	RISTICS						
Forward Voltage V <sub>SD</sub>	V <sub>SD</sub>	$V_{GS} = 0 V,$ $I_{S} = 3 A$	$T_{\rm J} = 25^{\circ} \rm C$		0.82	1.2	V
			T <sub>J</sub> = 125°C		0.68		
Reverse Recovery Time	t <sub>RR</sub>	$V_{GS}$ = 0 V, d <sub>IS</sub> /d <sub>t</sub> = 100 A/µs, V <sub>DS</sub> = 30 V, I <sub>S</sub> = 3 A			21		ns
Charge Time	ta				11		
Discharge Time	tb				10		
Reverse Recovery Charge	Q <sub>RR</sub>				9.7		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **TYPICAL CHARACTERISTICS**



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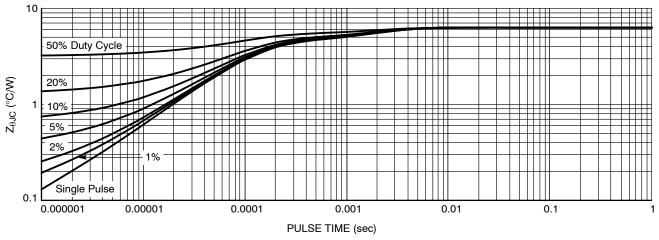


Figure 13. Thermal Response

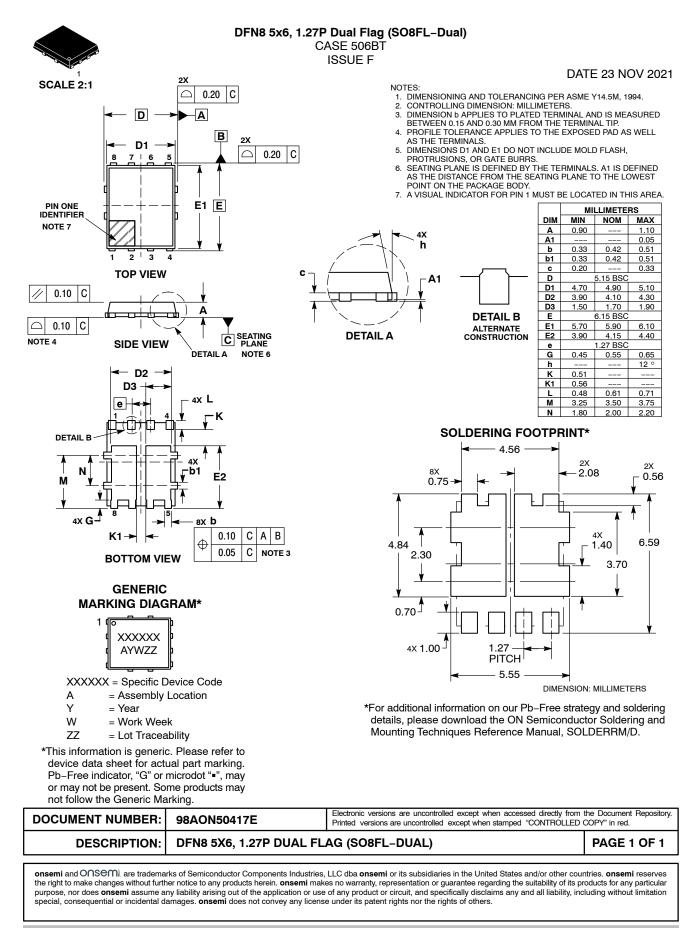
#### **DEVICE ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup>
NVMFD030N06CT1G	30DN6C	SO-8FL Dual (Pb-Free)	1500 / Tape & Reel
NVMFWD030N06CT1G	30DN6W	SO-8FL Dual (Pb-Free, Wettable Flanks)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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